



60NM60

Power MOSFET

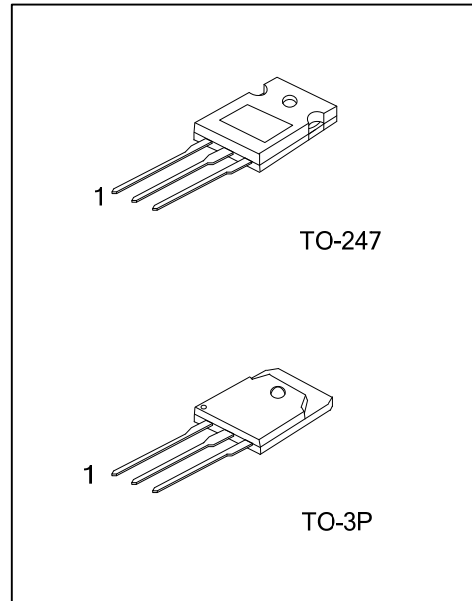
60A, 600V N-CHANNEL SUPER-JUNCTION MOSFET

DESCRIPTION

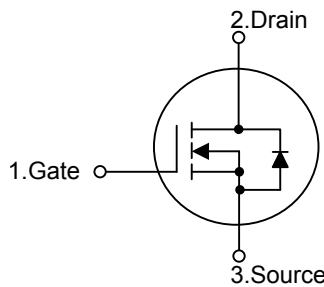
The **UTC 60NM60** is a Super Junction MOSFET Structure and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and a high rugged avalanche characteristics. This power MOSFET is usually used at DC-DC, AC-DC converters for power applications.

FEATURES

- * $R_{DS(ON)} < 65 \text{ m}\Omega @ V_{GS}=10\text{V}, I_D=30\text{A}$
- * High Switching Speed
- * 100% Avalanche Tested



SYMBOL



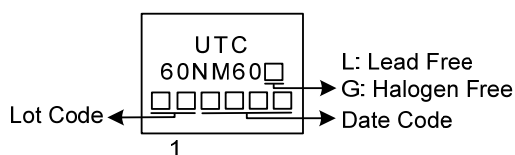
ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
60NM60L-T3P-T	60NM60G-T3P-T	TO-3P	G	D	S	Tube
60NM60L-T47-T	60NM60G-T47-T	TO-247	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>60NM60G-T3P-T</p>	<p>(1) T: Tube</p> <p>(2) T3P: TO-3P, T47: TO-247</p> <p>(3) G: Halogen Free and Lead Free, L: Lead Free</p>
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MARKING



■ ABSOLUTE MAXIMUM RATINGS ($T_C=25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	600	V
Gate-Source Voltage		V_{GSS}	± 30	V
Drain Current	Continuous	I_D	60	A
	Pulsed (Note 2)	I_{DM}	180	A
Avalanche Current (Note 2)		I_{AR}	10	A
Avalanche Energy		E_{AS}	1800	mJ
Power Dissipation	TO-247	P_D	320	W
	TO-3P		357	W
Junction Temperature		T_J	+150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. $L = 36\text{mH}$, $I_{AS} = 10\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-247	θ_{JA}	40	$^\circ\text{C/W}$
	TO-3P		30	$^\circ\text{C/W}$
Junction to Case	TO-247	θ_{JC}	0.39	$^\circ\text{C/W}$
	TO-3P		0.35	$^\circ\text{C/W}$

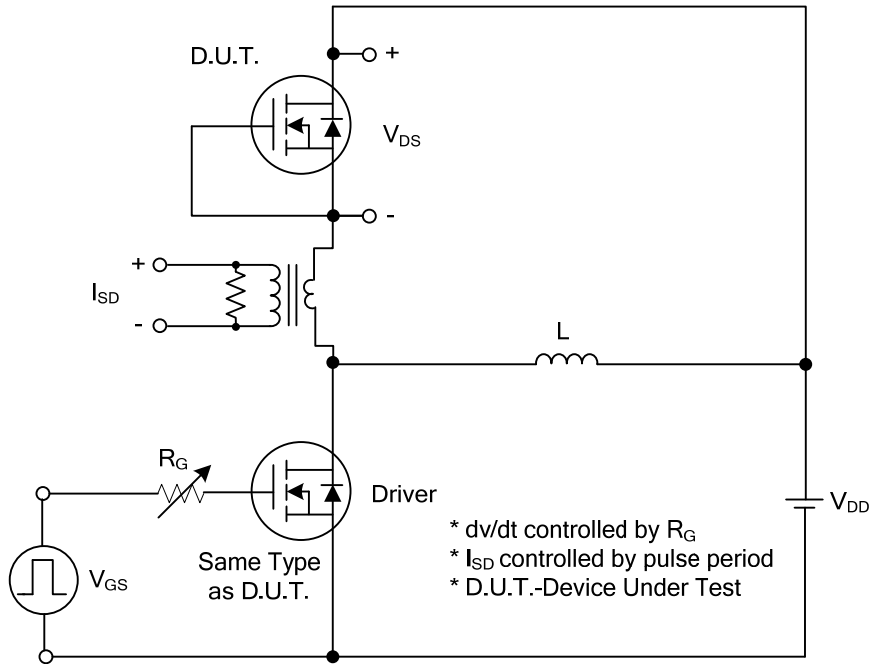
■ ELECTRICAL CHARACTERISTICS ($T_C=25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$I_D=250\mu\text{A}$, $V_{GS}=0\text{V}$	600			V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=600\text{V}$, $V_{GS}=0\text{V}$			50	μA
Gate- Source Leakage Current	Forward Reverse	I_{GSS}	$V_{GS}=+30\text{V}$, $V_{DS}=0\text{V}$ $V_{GS}=-30\text{V}$, $V_{DS}=0\text{V}$		+100	nA
					-100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	2.5		4.5	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10\text{V}$, $I_D=30\text{A}$			65	m Ω
DYNAMIC PARAMETERS						
Input Capacitance	C_{ISS}	$V_{GS}=0\text{V}$, $V_{DS}=25\text{V}$, $f=1.0\text{MHz}$		4900		pF
Output Capacitance	C_{OSS}			2730		pF
Reverse Transfer Capacitance	C_{RSS}			128		pF
SWITCHING PARAMETERS						
Total Gate Charge	Q_G	$V_{DS}=200\text{V}$, $V_{GS}=10\text{V}$, $I_D=60\text{A}$, (Note 1, 2)		156		nC
Gate to Source Charge	Q_{GS}			40		nC
Gate to Drain Charge	Q_{GD}			62		nC
Turn-ON Delay Time	$t_{D(ON)}$	$V_{DD}=30\text{V}$, $V_{GS}=10\text{V}$, $I_D=0.5\text{A}$, $R_G=25\Omega$ (Note 1, 2)		150		ns
Rise Time	t_R			500		ns
Turn-OFF Delay Time	$t_{D(OFF)}$			1400		ns
Fall-Time	t_F			823		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Body-Diode Continuous Current	I_S				60	A
Maximum Body-Diode Pulsed Current	I_{SM}				180	A
Drain-Source Diode Forward Voltage	V_{SD}	$I_S=60\text{A}$, $V_{GS}=0\text{V}$			1.4	V
Body Diode Reverse Recovery Time	t_{rr}	$I_S=30\text{A}$, $V_{GS}=0\text{V}$, $V_R=200\text{V}$		640		ns
Body Diode Reverse Recovery Charge	Q_{rr}	$dI_F/dt=100\text{A}/\mu\text{s}$ (Note 1)		14		μC

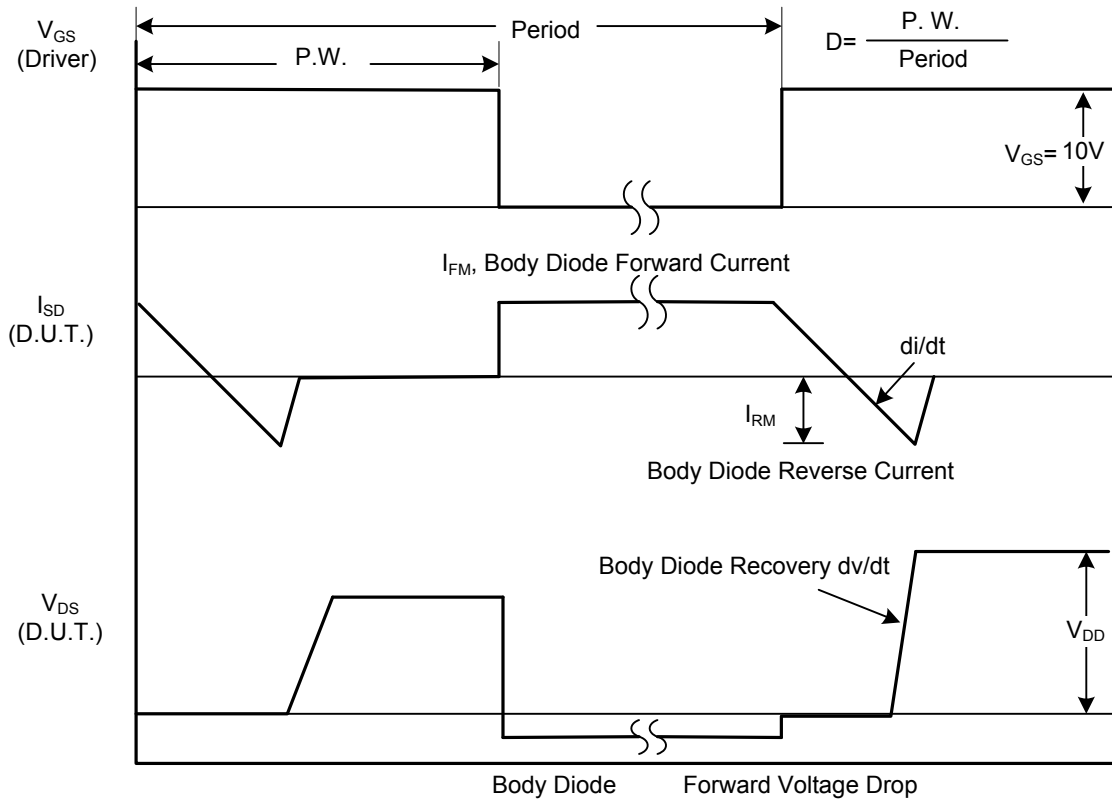
Notes: 1. Pulse Test : Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating ambient temperature.

■ TEST CIRCUITS AND WAVEFORMS



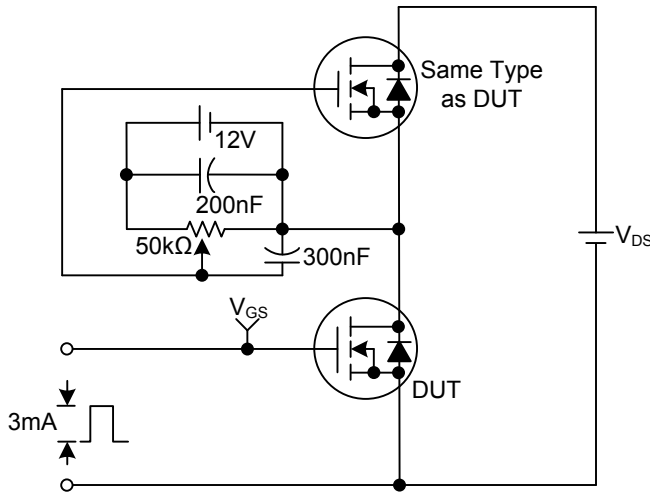
Peak Diode Recovery dv/dt Test Circuit



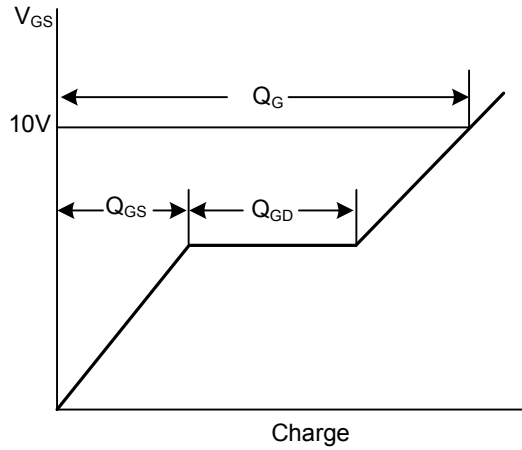
Peak Diode Recovery dv/dt Waveforms

■ TEST CIRCUITS AND WAVEFORMS

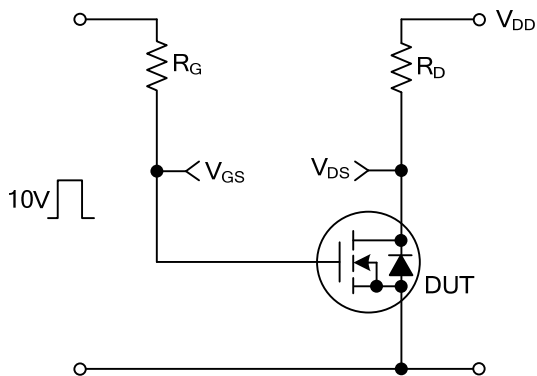
Gate Charge Test Circuit



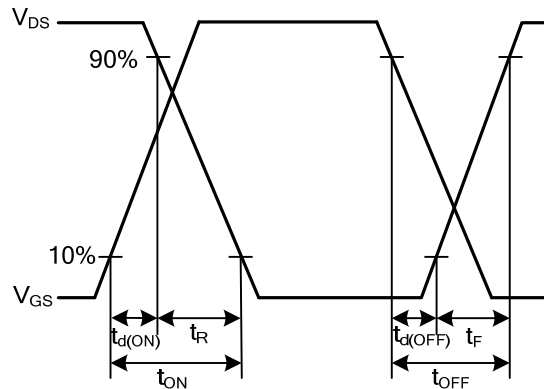
Gate Charge Waveforms



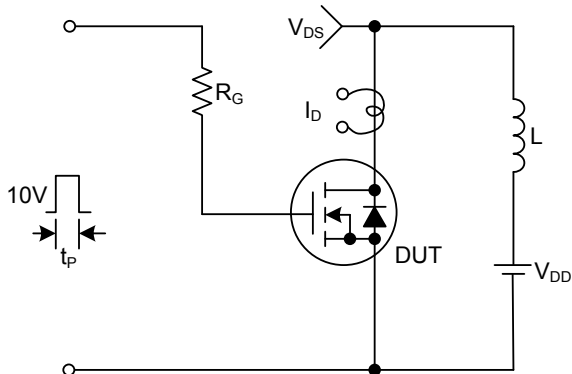
Resistive Switching Test Circuit



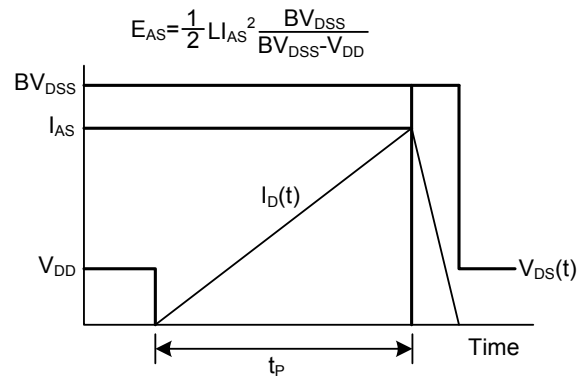
Resistive Switching Waveforms



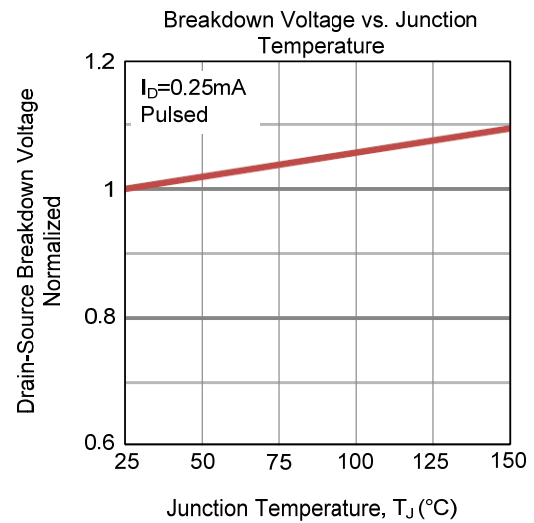
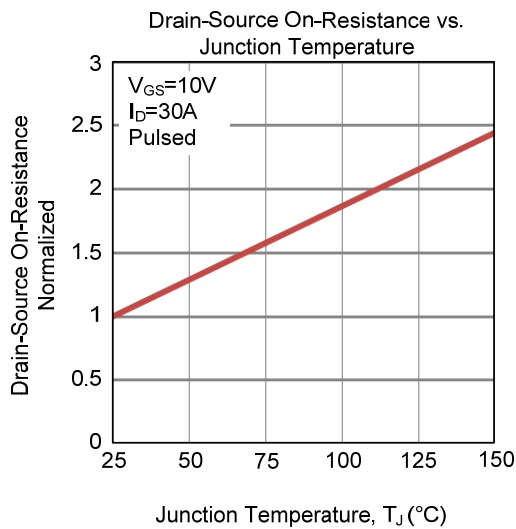
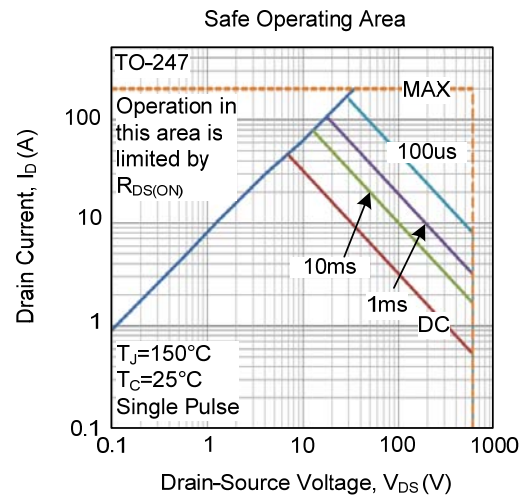
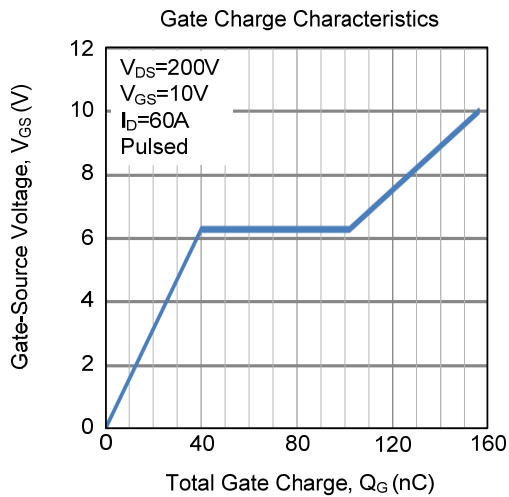
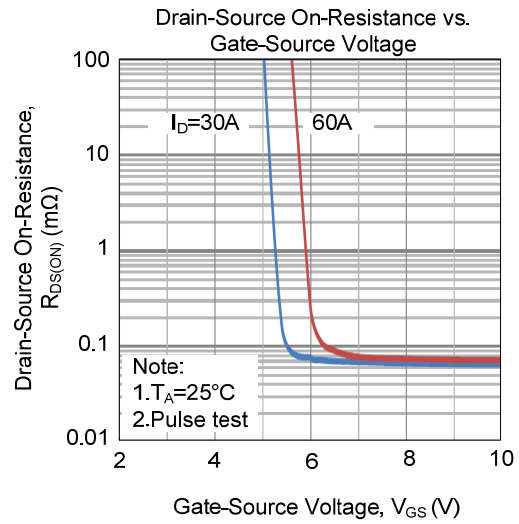
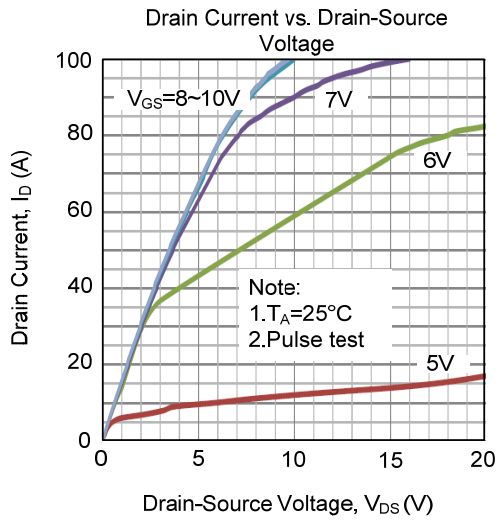
Unclamped Inductive Switching Test Circuit



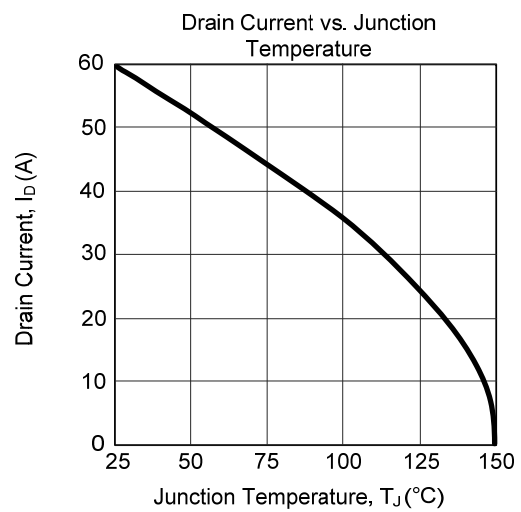
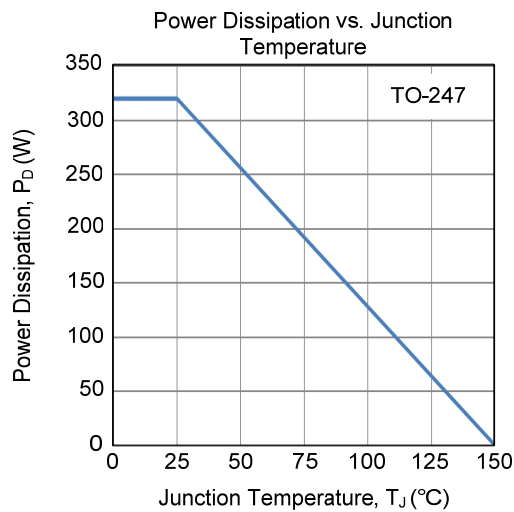
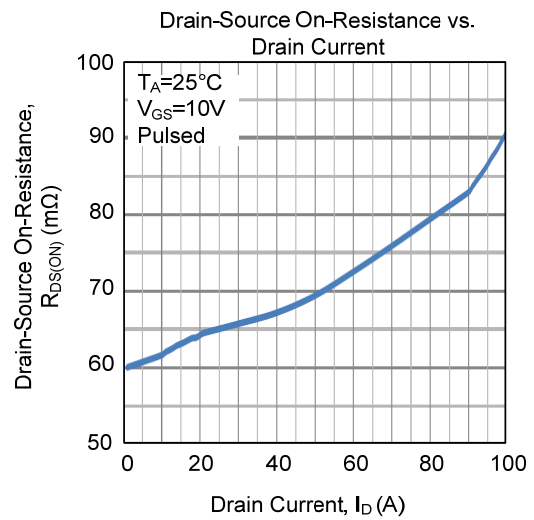
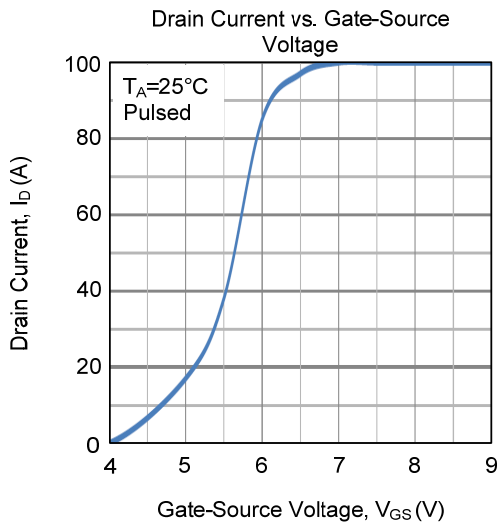
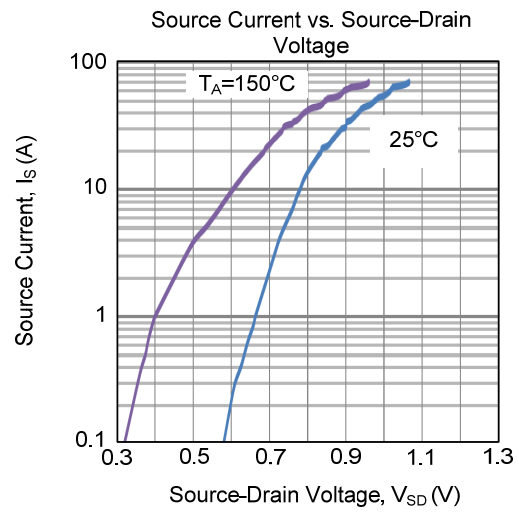
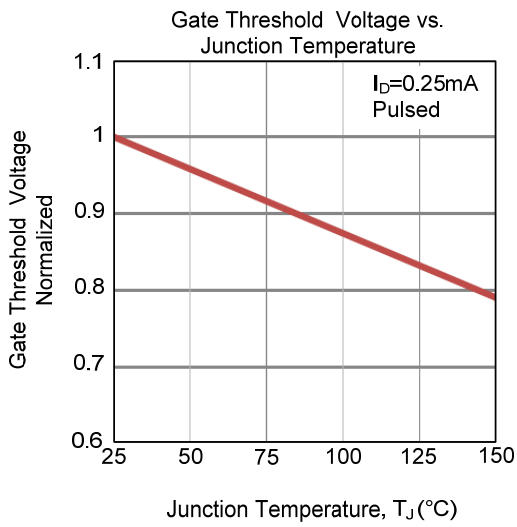
Unclamped Inductive Switching Waveforms



TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS (Cont.)



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